

# Homogeneously Doped Atomic Layer Deposition Zinc Tin Oxide Thin Films for Improving Contact Resistance in Semiconductor Device Applications

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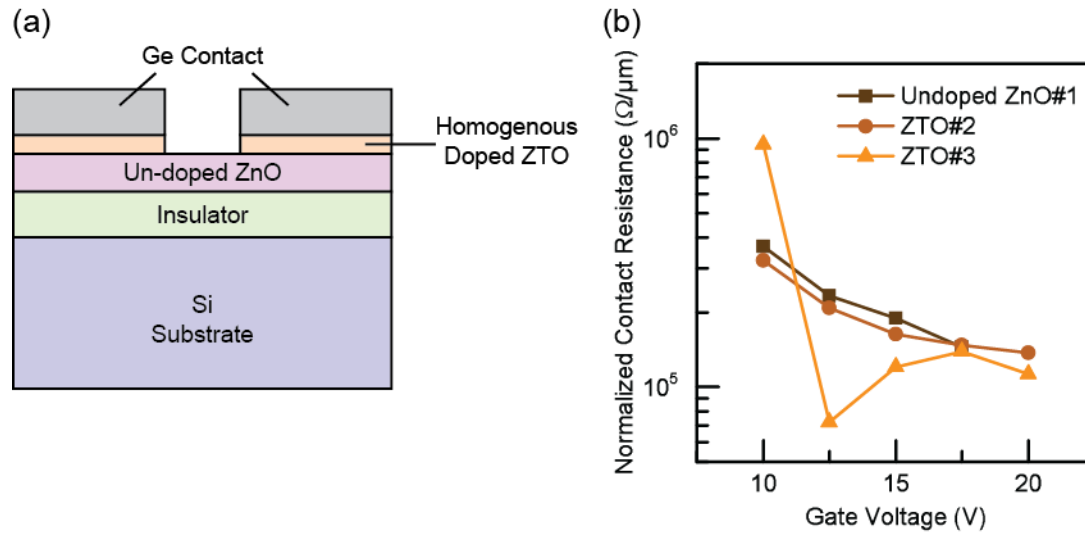


Fig. 1(a) Cross-section schematic of the device structure used to perform the gated transmission line method (TLM) analysis. (b) Extracted normalized contact resistance from the TLM analysis for un-doped ZnO and two doped ZTO films with increasing concentrations of tin – numbered in order from least doped (#1) to most (#3).